

# BTA01-800Q-HAF

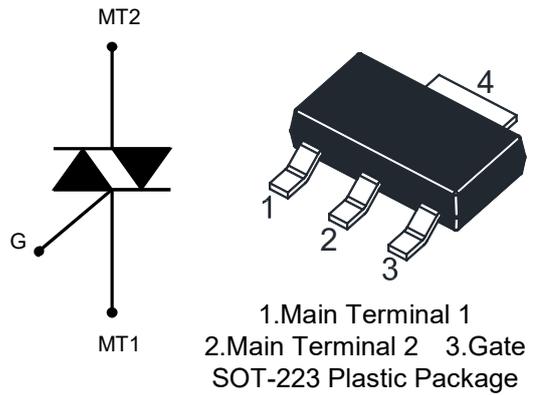
## Silicon Bidirectional Thyristors

### Features

- High blocking voltage capability
- Halogen and Antimony Free(HAF), RoHS compliant

### Applications

- General purpose low power motor control
- Industrial process control
- Low power AC Fan controllers
- Home appliances



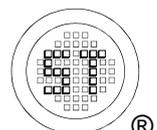
### Absolute Maximum Ratings ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Repetitive Peak off-State Voltage	$V_{\text{DRM}}$	800	V
Repetitive Peak Reverse Voltage	$V_{\text{RRM}}$	800	V
RMS on-State Current Full Sine Wave, $T_{\text{sq}} \leq 105^\circ\text{C}$	$I_{\text{T(RMS)}}$	1	A
Peak Non-repetitive Surge Current Full Sine Wave, $t_p = 20\text{ ms}$	$I_{\text{TSM}}$	9	A
Circuit Fusing Considerations $t_p = 10\text{ ms}$ , sine-wave pulse	$I^2t$	0.32	$\text{A}^2\text{s}$
Critical Rate-of-Rise of on-Sate Current at $I_{\text{T}} = 1\text{ A}$ , $I_{\text{G}} = 20\text{ mA}$ , $di_{\text{G}}/dt = 0.1\text{ A}/\mu\text{s}$	$di/dt$	50 50 50 20	$\text{A}/\mu\text{s}$
Peak Gate Current	$I_{\text{GM}}$	1	A
Peak Gate Power	$P_{\text{GM}}$	2	W
Average Gate Power Dissipation (Over any 20 ms period)	$P_{\text{G(AV)}}$	0.1	W
Operating Junction Temperature Range	$T_J$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{\text{Stg}}$	- 40 to + 150	$^\circ\text{C}$

### Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction to Ambient <sup>1)</sup>	$R_{\theta\text{JA}}$	70	$^\circ\text{C}/\text{W}$

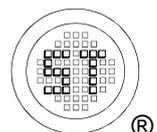
<sup>1)</sup> Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.



# BTA01-800Q-HAF

## Characteristics at $T_j = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Max.	Unit
Peak Forward or Reverse Blocking Current at $V_{\text{DRM}} / V_{\text{RRM}}, T_j = 125^\circ\text{C}$	$I_{\text{DRM}}, I_{\text{RRM}}$	-	0.5	mA
Peak Forward on-State Voltage at $I_T = 1.4 \text{ A}$	$V_T$	-	1.6	V
Gate Trigger Current at $V_D = 12 \text{ V}, I_T = 0.1 \text{ A}$	$I_{\text{GT}}$	-	10	mA
	T2+G+	-	10	
	T2+G-	-	10	
	T2-G-	-	10	
	T2-G+	-	10	
Holding Current at $V_D = 12 \text{ V}$	$I_H$	-	10	mA
Latching Current at $V_D = 12 \text{ V}, I_G = 0.1 \text{ A}$	$I_L$	-	15	mA
	T2+G+	-	25	
	T2+G-	-	15	
	T2-G-	-	15	
	T2-G+	-	15	
Gate Trigger Voltage at $V_D = 12 \text{ V}, I_T = 0.1 \text{ A}, T_j = 25^\circ\text{C}$ at $V_D = 800 \text{ V}, I_T = 0.1 \text{ A}, T_j = 125^\circ\text{C}$	$V_{\text{GT}}$	- 0.2	1.3 -	V
Rate of Rise of Off-State Voltage at $V_{\text{DM}} = 536 \text{ V}, T_j = 110^\circ\text{C}$ , gate open circuit	$dV_D/dt$	50	-	V/ $\mu\text{s}$



# BTA01-800Q-HAF

## Electrical Characteristics Curves

Fig.1 RMS on-State Current vs.  $T_{sq}$

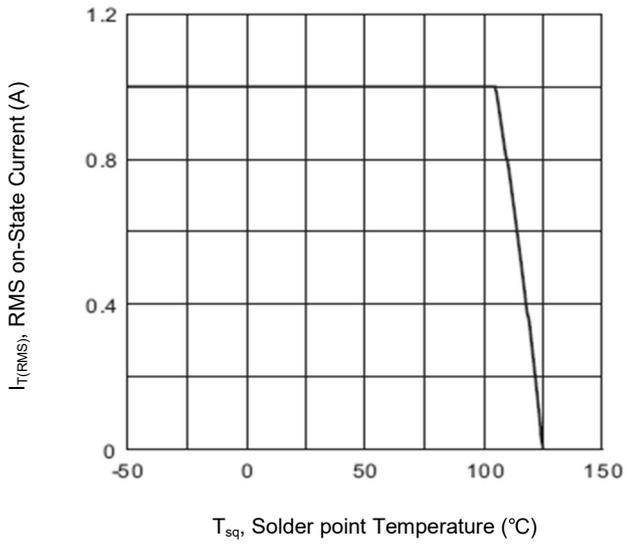


Fig.2 RMS on-State Current vs. Surge duration

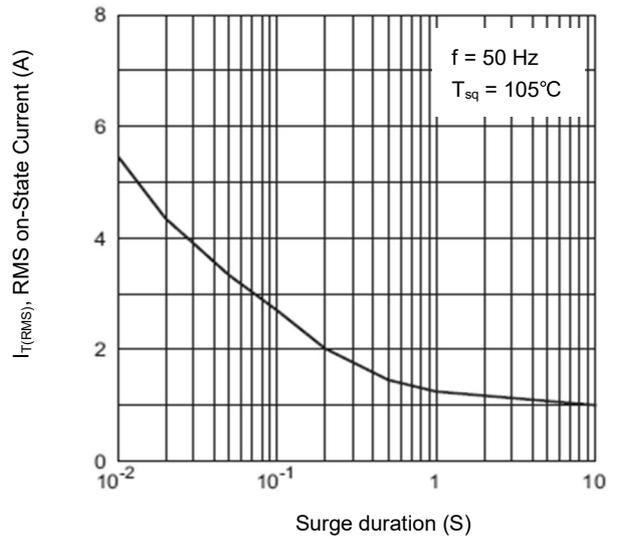
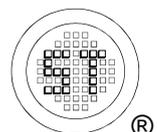
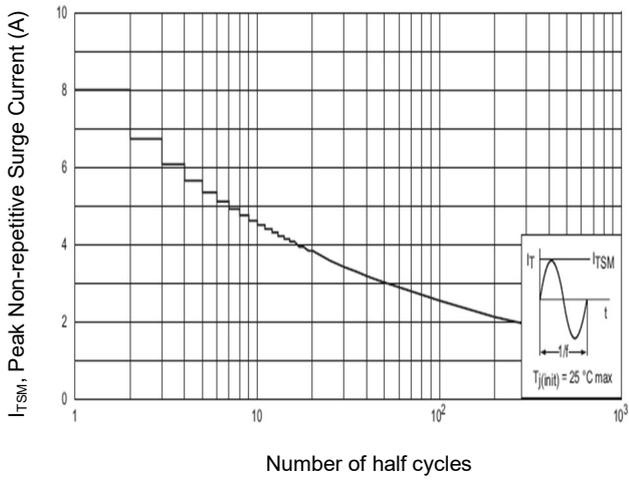


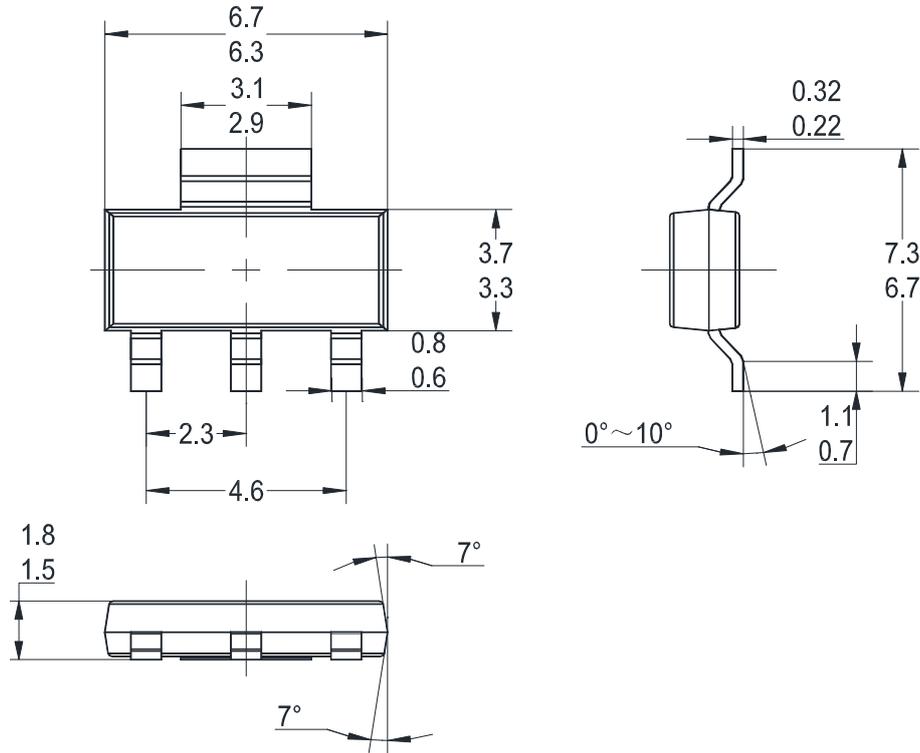
Fig.3 Surge Peak on-State Current vs. number of Cycles



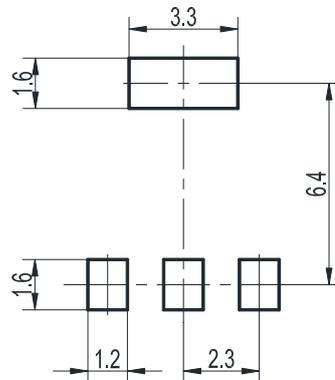
# BTA01-800Q-HAF

## Package Outline (Dimensions in mm)

SOT-223



## Recommended Soldering Footprint



## Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-223	12	8 ± 0.1	0.315 ± 0.004	330	13	3,000

## Marking information

" BTA01-800Q " = Part No.

" \*\*\*\*\* " = Date Code Marking

Font type: Arial

